

N-Channel MOSFETs (>500V...900V); Package: PG-TO263-3; VDS (max): 600.0 V;
 Package: D2PAK (TO-263); RDS(ON) @ TJ=25°C VGS=10: 99.0 mOhm; ID(max) @
 TC=25°C: 38.0 A; IDpuls (max): 112.0 A;

Manufacturers	<u>Infineon Technologies Corporation</u>
Package/Case	TO-263 (D2PAK)
Product Type	Transistors
RoHS	Rohs
Lifecycle	



Images are for reference only

Please submit RFQ for IPB60R099C6 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

The IPB60R099C6 is a high-voltage power MOSFET designed for efficient power switching. It features low on-resistance and high current handling capabilities, making it suitable for applications that require high power and efficiency.

Features

- N-channel MOSFET
- High voltage rating
- Low on-resistance (RDS(on))
- High current handling capability
- Fast switching speed
- Low gate charge

Application

- Power supplies
- Motor control
- Industrial automation
- Electric vehicles
- Solar inverters
- Switching regulators
- LED lighting
- Audio amplifiers





Related Products



[IPP60R070CFD7](#)

Infineon Technologies Corporation
TO-220-3



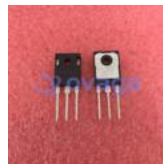
[IPB180N06S4-H1](#)

Infineon Technologies Corporation
PG-TO263-7-3



[IPG20N04S4-12](#)

Infineon Technologies Corporation
TDSON-8



[IPW65R080CFD](#)

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TO-247



[IPD25N06S4L-30](#)

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PG-TO252-3



[IPD180N10N3G](#)

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